

***Please replace the abstract with the following amended abstract:***

~~There is disclosed a~~ A method for using a computer to calculate a pileup state of an impurity in an interface between an Si layer in which a source and a drain are formed, and an SiO<sub>2</sub> layer brought in contact with the Si layer at a high speed[[.]]  
[[First]], wherein data is first set assuming that the Si layer is constituted of a plurality of cells. Subsequently, the impurity is moved to a pileup position of the interface from each cell, and an amount of impurity piled up in each pileup position of the interface is calculated. In this case, a mass of the impurity moving to the interface from each cell is determined as a function of a distance to each pileup position from each cell, and a distance to a source or a drain closest to the cell.